

Product Introduction

Our InAs (Indium Arsenide) wafers are grown using the Vertical Gradient Freeze (VGF) method, available in 2", 3", and 4" diameters with <100> and <111> orientations. Offered in undoped and doped variants (N-type: S, Sn; P-type: Zn), these epi-ready wafers feature low TTV ($\leq 15\mu\text{m}$), bow ($\leq 10\mu\text{m}$), and warp ($\leq 15\mu\text{m}$) for consistent downstream processing. With polished or etched surface finishes, our InAs wafers are well suited for infrared and high-speed electronic device applications.

Applications

- Infrared photodetectors and lasers
- High-speed, low-power transistors (due to high electron mobility)
- Thermophotovoltaic (TPV) cells
- Quantum well and quantum dot device structures

INDIUM ARSENIDE (INAS) WAFER SPECIFICATIONS			
GROWTH METHOD	VGF		
Type/Dopant	Undoped // N/S/Sn // P/Zn		
Diameter(mm)	50.8 $\pm$ 0.3	76.2 $\pm$ 0.3	100 $\pm$ 0.3
Thickness(um)	500 $\pm$ 25	600 $\pm$ 25	800 $\pm$ 25
OF(mm)	16 $\pm$ 2	22 $\pm$ 2	32.5 $\pm$ 2
IF(mm)	8 $\pm$ 2	12 $\pm$ 2	18 $\pm$ 2
Orientation	<100>, <111>		
TTV(um)	≤ 10	≤ 10	≤ 15
Bow(um)	≤ 10	≤ 10	≤ 15
Wrap(um)	≤ 15	≤ 15	≤ 15
Surface	Polished/Etched		
Epi-ready	Yes		